

## Supporting Information

### **Realization of an efficient electron source by ultraviolet-light-assisted field emission from a one-dimensional ZnO nanorods/n-GaN heterostructure photoconductive detector**

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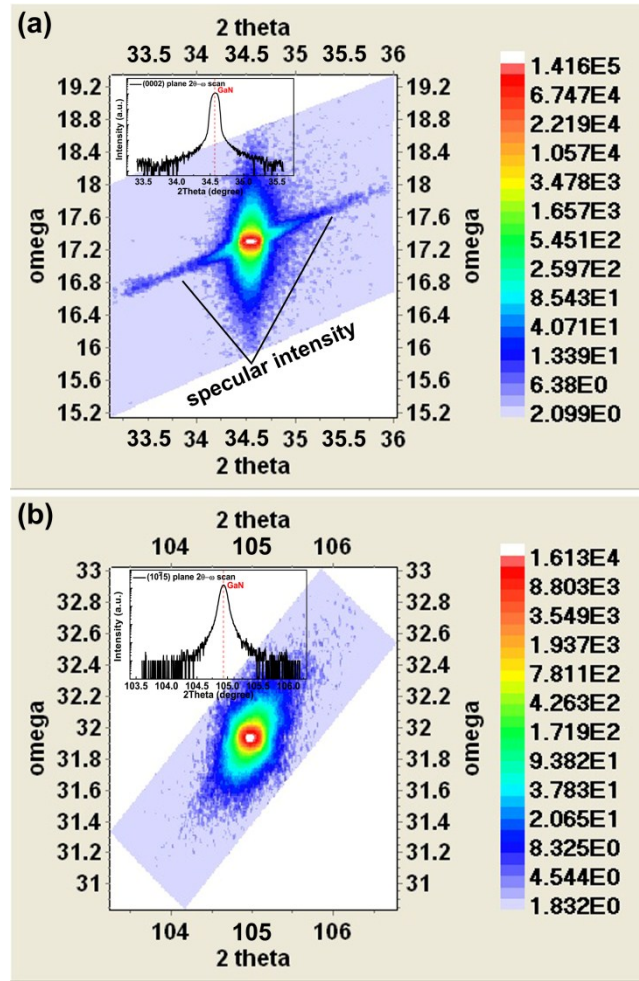


Fig. S1. Reciprocal space mapping (RSM) obtained by a high-resolution X-ray diffractometer. (a) The symmetrical RSM around the (0002) reflection for as-fabricated n-GaN epilayer. The inset shows its corresponding  $2\theta$ - $\omega$  scanning curve. (b) The asymmetrical RSM around the (105) reflection for as-fabricated n-GaN epilayer. The inset shows its corresponding  $2\theta$ - $\omega$  scanning curve.